# VS-UFL80FA60

**Vishay Semiconductors** 

# Insulated Ultrafast Rectifier Module, 80 A



| PRIMARY CHARACTERISTICS                          |                          |  |  |  |  |  |
|--|--------------------------|--|--|--|--|--|
| V <sub>R</sub>                                   | 600 V                    |  |  |  |  |  |
| $I_{F(AV)}$ per module at $T_C = 115 \text{ °C}$ | 80 A                     |  |  |  |  |  |
| t <sub>rr</sub>                                  | 41 ns                    |  |  |  |  |  |
| Туре   | Modules - diode FRED Pt® |  |  |  |  |  |
| Package  | SOT-227                  |  |  |  |  |  |

## **FEATURES**

- Two fully independent diodes
- · Fully insulated package
- Ultrafast, soft reverse recovery, with high RoHS COMPLIANT operation junction temperature ( $T_{\perp}$  max. = 175 °C)
- Low forward voltage drop
- · Optimized for power conversion: welding and industrial SMPS applications
- Easy to use and parallel
- Industry standard outline
- UL approved file E78996
- Designed and gualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## **DESCRIPTION / APPLICATIONS**

The VS-UFL80FA60 insulated modules integrate two state of the art ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The diodes structure, and its life time control, provide an ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, DC/DC converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

| ABSOLUTE MAXIMUM RATINGS                    |                                   |                                 |             |       |  |  |  |
|---|-----------------------------------|---------------------------------|-------------|-------|--|--|--|
| PARAMETER                                   | SYMBOL                            | TEST CONDITIONS                 | MAX.        | UNITS |  |  |  |
| Cathode to anode voltage                    | VR                                |                                 | 600         | V     |  |  |  |
| Continuous forward current per diode        | I <sub>F</sub>                    | T <sub>C</sub> = 85 °C          | 65          | А     |  |  |  |
| Single pulse forward current per diode      | I <sub>FSM</sub>                  | T <sub>C</sub> = 25 °C          | 300         | A     |  |  |  |
| Maximum power dissipation per module        | PD                                | T <sub>C</sub> = 85 °C          | 176         | W     |  |  |  |
| RMS isolation voltage                       | V <sub>ISOL</sub>                 | Any terminal to case, t = 1 min | 2500        | V     |  |  |  |
| Operating junction and storage temperatures | T <sub>J</sub> , T <sub>Stg</sub> |                                 | -55 to +175 | °C    |  |  |  |





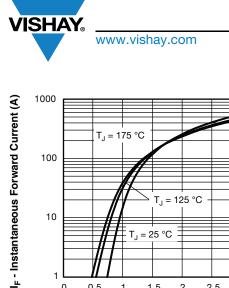


| <b>ELECTRICAL SPECIFICATIONS PER DIODE</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified) |                 |   |              |      |      |       |    |
|--|-----------------|---|--------------|------|------|-------|----|
| PARAMETER  | SYMBOL          | TEST COND                                       | MIN.         | TYP. | MAX. | UNITS |    |
| Cathode to anode breakdown voltage   | V <sub>BR</sub> | I <sub>R</sub> = 100 μA                         |              | 600  | -    | -     |    |
| Forward voltage  | V <sub>FM</sub> | I <sub>F</sub> = 30 A                           | -            | 1.1  | 1.43 |       |    |
|  |                 | I <sub>F</sub> = 60 A                           |              | -    | 1.27 | 1.49  | V  |
|  |                 | I <sub>F</sub> = 30 A                           | T.I = 125 °C | -    | 1.0  | 1.23  |    |
|  |                 | I <sub>F</sub> = 60 A                           | 1j = 125 C   | -    | 1.17 | 1.35  |    |
|  |                 | $V_{R} = V_{R}$ rated                           |              | -    | 0.1  | 50    | μA |
| Reverse leakage current  | I <sub>RM</sub> | $T_J = 175 \text{ °C}, V_R = V_R \text{ rated}$ |              | -    | 0.2  | 1.0   | mA |
| Junction capacitance   | CT              | V <sub>R</sub> = 600 V                          |              | -    | 30   | -     | pF |

| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified) |                  |                         |   |      |      |       |     |  |
|---|------------------|-------------------------|---|------|------|-------|-----|--|
| PARAMETER   | SYMBOL           | TEST                    | MIN.  | TYP. | MAX. | UNITS |     |  |
| Reverse recovery time   | t <sub>rr</sub>  | T <sub>J</sub> = 25 °C  | $    I_F = 1 \text{ A}; \\ dI_F/dt = 200 \text{ A}/\mu\text{s}; \\ V_R = 30 \text{ V} $ | -    | 41   | -     | ns  |  |
| neverse recovery time   | ۲rr              | T <sub>J</sub> = 25 °C  | I <sub>F</sub> = 30 A<br>dI <sub>F</sub> /dt = 200 A/μs<br>V <sub>B</sub> = 200 V       | -    | 115  | -     | 113 |  |
|   |                  | T <sub>J</sub> = 125 °C |   | -    | 200  | -     |     |  |
| Deale receiver a current  | I <sub>RRM</sub> | T <sub>J</sub> = 25 °C  |   | -    | 11   | -     | А   |  |
| Peak recovery current   |                  | T <sub>J</sub> = 125 °C |   | -    | 20   | -     | A   |  |
|   | 0                | T <sub>J</sub> = 25 °C  | •R - 200 •  | -    | 600  | -     | nC  |  |
| Reverse recovery charge Q <sub>rr</sub>   |                  | T <sub>J</sub> = 125 °C |   | -    | 1900 | -     | lic |  |

| THERMAL - MECHANICAL SPECIFICATIONS     |                   |                       |      |         |            |             |
|---|-------------------|-----------------------|------|---------|------------|-------------|
| PARAMETER                               | SYMBOL            | TEST CONDITIONS       | MIN. | TYP.    | MAX.       | UNITS       |
| Junction to case, single leg conducting | Б                 |                       | -    | -       | 1.02       |             |
| Junction to case, both leg conducting   | R <sub>thJC</sub> | -                     | -    | 0.51    | °C/W       |             |
| Case to heatsink                        | R <sub>thCS</sub> | Flat, greased surface | -    | 0.10    | -          |             |
| Weight                                  |                   |                       | -    | 30      | -          | g           |
| Mounting torque                         |                   | Torque to terminal    | -    | -       | 1.1 (9.7)  | Nm (lbf.in) |
| Mounting torque                         |                   | Torque to heatsink    | -    | -       | 1.8 (15.9) | Nm (lbf.in) |
| Case style                              |                   |                       |      | SOT-227 |            |             |





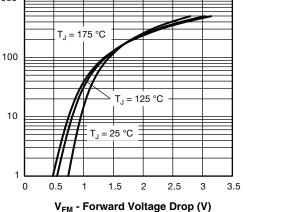


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Leg)

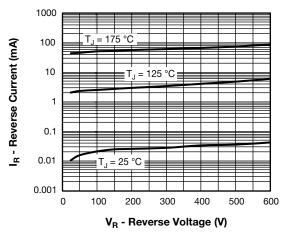


Fig. 2 - Typical Values of Reverse Current vs. **Reverse Voltage** 

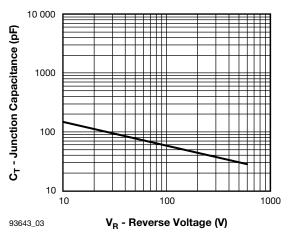


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

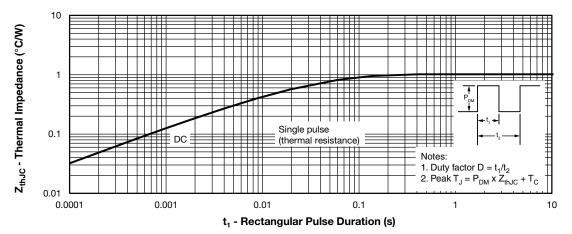
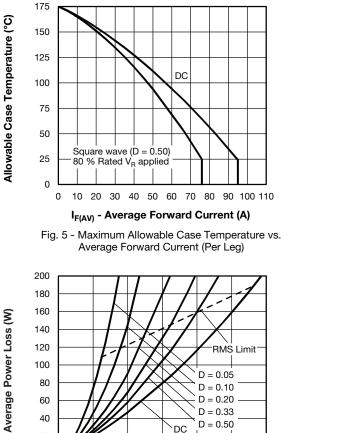
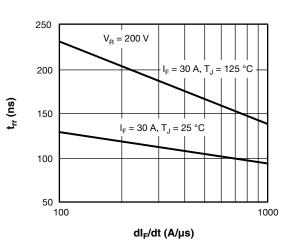


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics (Per Leg)

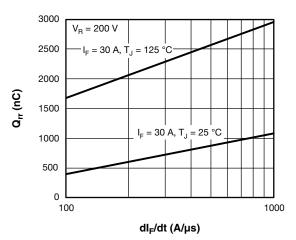
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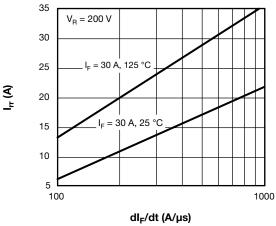


Fig. 9 - Typical Stored Current vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

40

60

Average Forward Current - I<sub>F(AV)</sub> (A)

Fig. 6 - Forward Power Loss Characteristics (Per Leg)

80

100

120

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see fig. 6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

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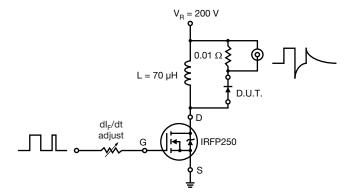


Fig. 10 - Reverse Recovery Parameter Test Circuit

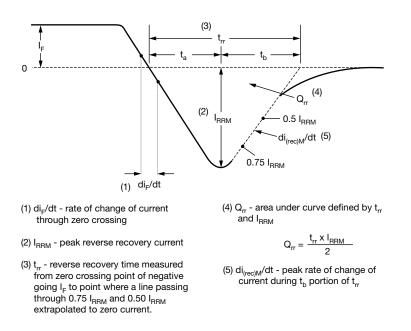


Fig. 11 - Reverse Recovery Waveform and Definitions





## **ORDERING INFORMATION TABLE**

| Device code | vs- | UF  | L         | 80        | F         | Α       | 60       |
|-------------|-----|---|-----------|-----------|-----------|---------|----------|
|             |     | 2   | 3         | 4         | 5         | 6       | 7        |
|             | 1 - | Visł  | nay Sem   | niconduc  | ctors pro | oduct   |          |
|             | 2 - | - Ultrafast rectifier                       |           |           |           |         |          |
|             | 3 - | - Ultrafast Pt diffused, Low V <sub>F</sub> |           |           |           |         |          |
|             | 4 - | Cur   | rent rati | ng (80 =  | 80 A)     |         |          |
|             | 5 - | Circ  | uit conf  | iguratior | n (two s  | eparate | diodes   |
|             | 6 - | Pac   | kage in   | dicator ( | SOT-22    | 7 stand | lard ins |
|             | 7 - | Volt  | age rati  | ng (60 =  | = 600 V)  |         |          |

| CIRCUIT CONFI                            | GURATION                      |                 |
|--|-------------------------------|-----------------|
| CIRCUIT                                  | CIRCUIT<br>CONFIGURATION CODE | CIRCUIT DRAWING |
| Two separate diodes,<br>parallel pin-out | F                             | Lead Assignment |

| LINKS TO RELATED DOCUMENTS |                          |  |  |  |  |  |
|----------------------------|--------------------------|--|--|--|--|--|
| Dimensions                 | www.vishay.com/doc?95423 |  |  |  |  |  |
| Packaging information      | www.vishay.com/doc?95425 |  |  |  |  |  |



SOT-227 Generation 2

### **DIMENSIONS** in millimeters (inches)



#### Note

• Controlling dimension: millimeter



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